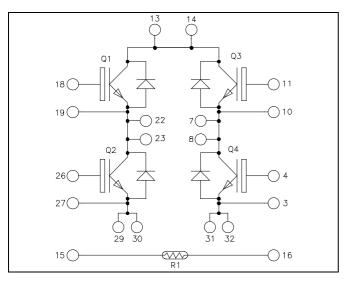


Full - Bridge Trench + Field Stop IGBT3 Power Module

 $V_{CES} = 600V$ $I_C = 75A$ @ Tc = 80°C



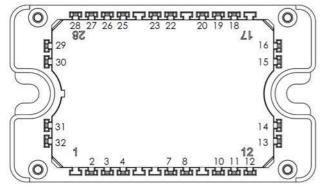
Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

• Trench + Field Stop IGBT3

- Low voltage drop
- Low tail current
- Switching frequency up to 20 kHz
- Low leakage current
- RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring



All multiple inputs and outputs must be shorted together Example: 13/14; 29/30; 22/23 ...

Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS compliant

All ratings @ $T_i = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings (per IGBT)

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Voltage		600	V
т	Continuous Collector Coment	$T_C = 25^{\circ}C$	100	
$I_{\rm C}$	Continuous Collector Current	$T_C = 80$ °C	75	A
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	140	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Power Dissipation	$T_C = 25^{\circ}C$	250	W
RBSOA	Reverse Bias Safe Operating Area	$T_{\rm J} = 150^{\circ}{\rm C}$	150A @ 550V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.



Electrical Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				250	μΑ
V _{CE(sat)}	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		1.5	1.9	V
		$I_C = 75A$	$T_j = 150$ °C		1.7		·
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 600 \mu A$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V$, $V_{CE} = 0V$				600	nA

Dynamic Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions			Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			4620		
Coes	Output Capacitance	$V_{CE} = 25V$			300		pF
C_{res}	Reverse Transfer Capacitance	f = 1MHz		140			
T _{d(on)}	Turn-on Delay Time	Inductive Switch	ning (25°C)		110		
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$			45		ns
T _{d(off)}	Turn-off Delay Time	$V_{\text{Bus}} = 300V$ $I_{\text{C}} = 75A$			200		
T_{f}	Fall Time	$R_G = 4.7\Omega$		40			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch $V_{GE} = \pm 15V$	ning (150°C)		120		
T_{r}	Rise Time	$\begin{array}{c} V_{Bus} = 300V \\ I_C = 75A \end{array}$			50		ns
$T_{d(off)}$	Turn-off Delay Time				250		
$T_{\rm f}$	Fall Time	$R_G = 4.7\Omega$			60		
Eon	Turn on Switching Engrav	$ \begin{array}{c c} V_{GE} = \pm 15 V & T_j = 25^{\circ} C \\ V_{Bus} = 300 V & T_j = 150^{\circ} C \end{array} $	$T_j = 25$ °C		0.35		mJ
Lon	Turn-on Switching Energy			0.6		1113	
Е	Turn-off Switching Energy	$I_C = 75A$	$T_j = 25$ °C	_	2.2		ın I
$E_{ m off}$		$R_G = 4.7\Omega \qquad T_j = 150^{\circ}C$		2.6		mJ	
R_{thJC}	Junction to Case Thermal Resistance					0.6	°C/W

Reverse diode ratings and characteristics (per diode)

Symbol	Characteristic Test Conditions			Min	Typ	Max	Unit
V_{RRM}	Peak Repetitive Reverse Voltage					600	V
I_{RM}	Reverse Leakage Current	V _R =600V				250	μΑ
I_F	DC Forward current		$Tc = 40^{\circ}C$		75		A
V_{F}	Diode Forward Voltage	$I_F = 75A$ $V_{GE} = 0V$	$T_j = 25$ °C		1.6	2	
V F			$T_j = 150$ °C		1.5		V
	t _{rr} Reverse Recovery Time		$T_j = 25$ °C		100		ns
rr rr		$T_j = 150$ °C		150		113	
	O_{rr} Reverse Recovery Charge $V_R = 300 V$	$T_j = 25$ °C		3.6		μC	
Qп			$T_j = 150$ °C		7.6		μΟ
Б	Davidas Dagavami Engara		$T_j = 25^{\circ}C$		0.85		mJ
E_{r}	Reverse Recovery Energy		$T_j = 150$ °C		1.8		1113
R_{thJC}	Junction to Case Thermal Resistance					0.98	°C/W



Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C	sistance @ 25°C		50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B _{25/85}	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta \mathrm{B/B}$		T _C =100°C		4		%

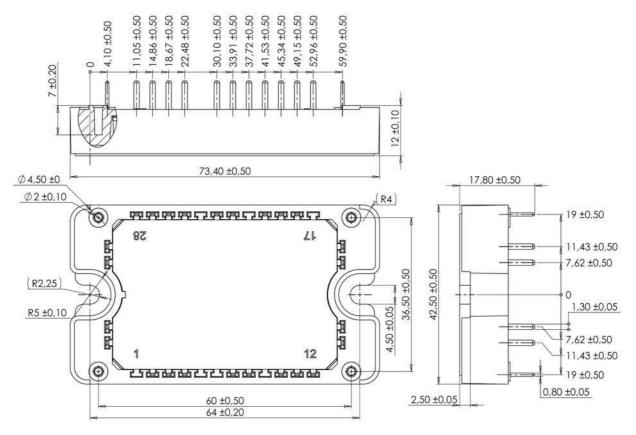
$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$

$$R_T: \text{ Thermistor value at T}$$

Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000		V
T_{J}	Operating junction temperature range			-40	175	
T_{JOP}	Recommended junction temperature under switching conditions			-40	T _J max -25	°C
T_{STG}	Storage Temperature Range			-40	125	
$T_{\rm C}$	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

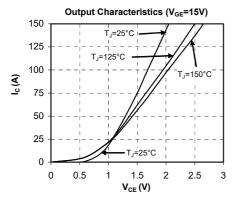
Package outline (dimensions in mm)

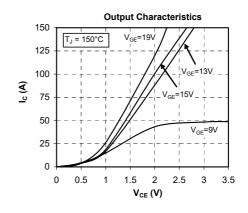


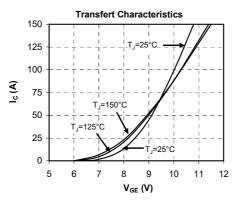
See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

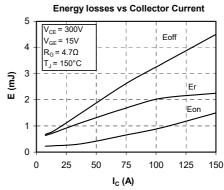


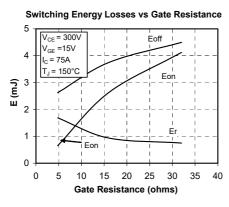
Typical Performance Curve

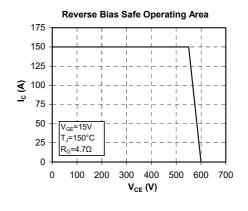


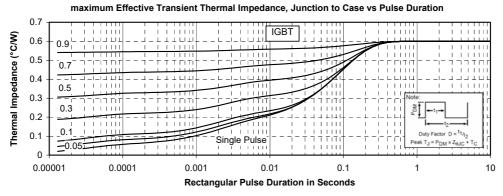




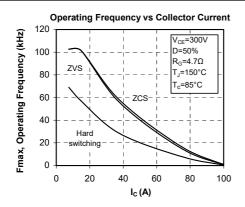


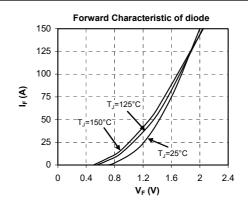


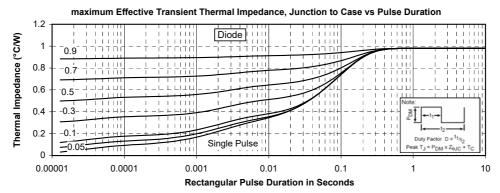












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